

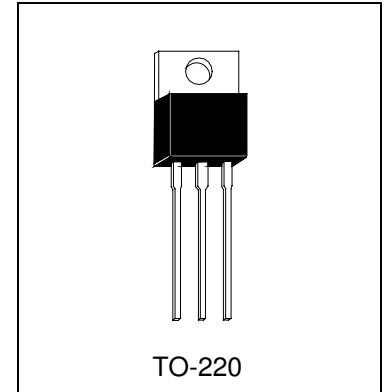


HMJE3055T

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HMJE3055T is designed for general purpose of amplifier and switching applications.



Absolute Maximum Ratings (T_A=25°C)

- Maximum Temperature
Storage Temperature -55 ~ +150 °C
Junction Temperature 150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation (T_C=25°C) 75 W
Total Power Dissipation (T_A=25°C) 0.6 W
- Maximum Voltages and Currents (T_A=25°C)
BV_{CBO} Collector to Base Voltage 70 V
BV_{CEO} Collector to Emitter Voltage 60 V
BV_{EBO} Emitter to Base Voltage 5 V
I_C Collector Current 10 A
I_B Base Current 6 A

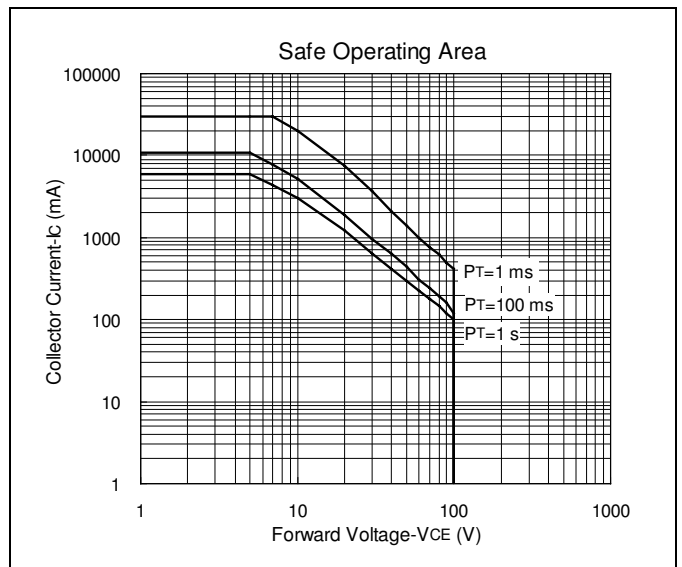
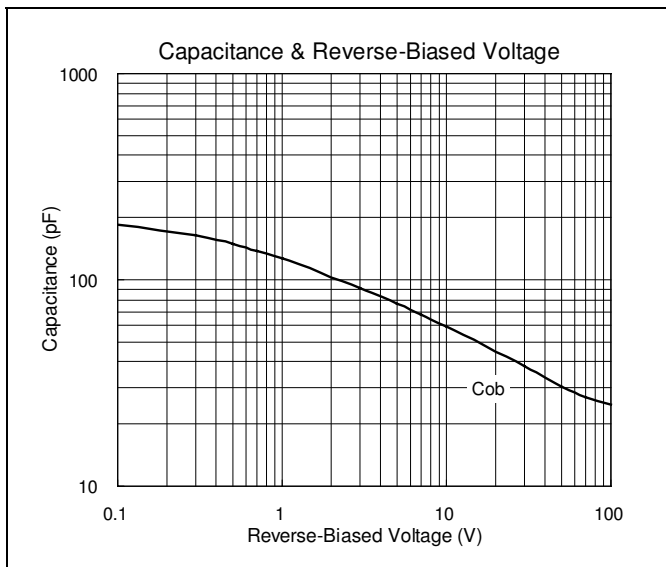
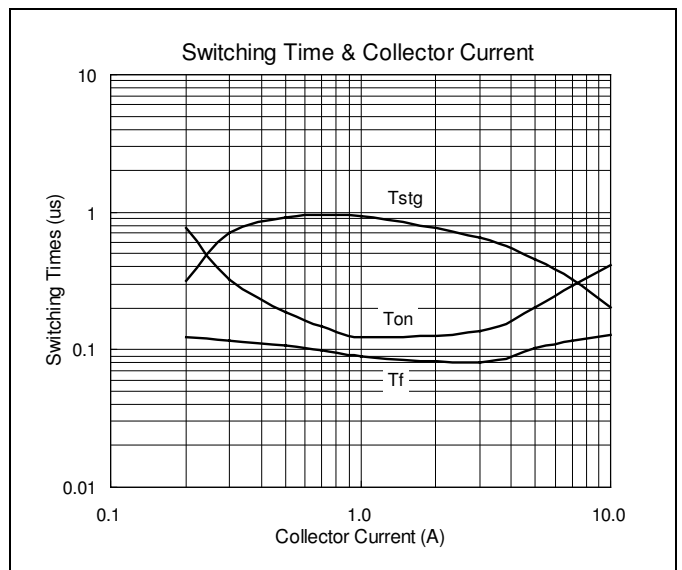
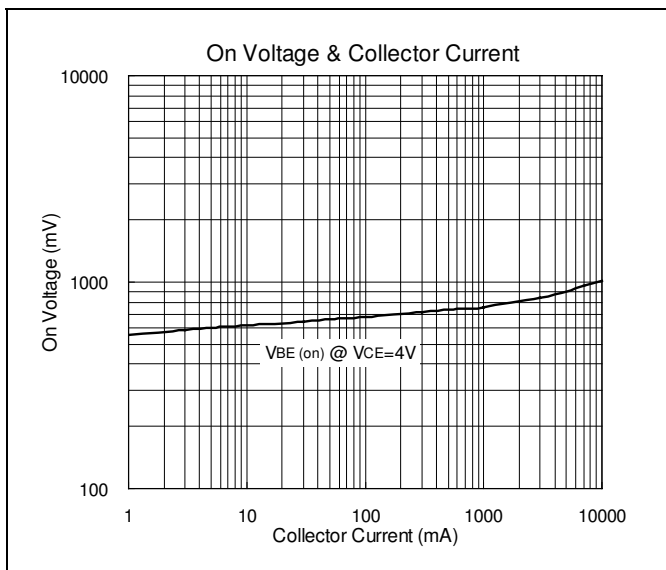
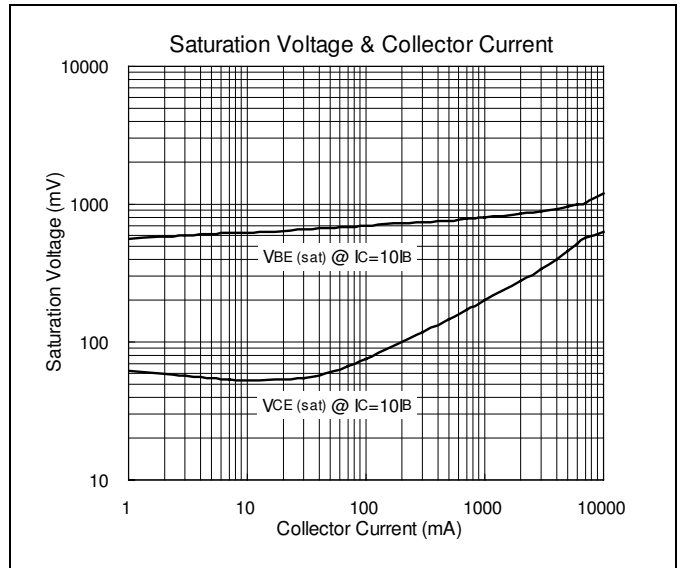
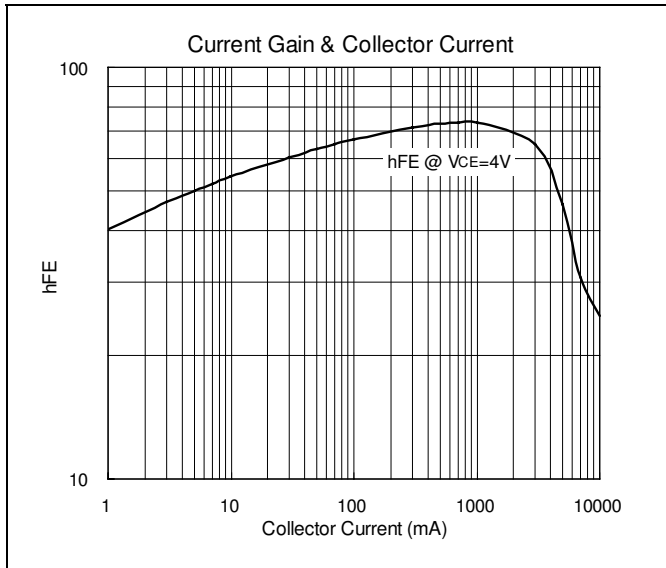
Electrical Characteristics (T_A=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CEO}	60	-	-	V	I _C =200mA, I _B =0
BV _{CBO}	70	-	-	V	I _C =10mA, I _E =0
BV _{EBO}	5	-	-	V	I _E =10mA, I _C =0
I _{CBO}	-	-	1.	mA	V _{CB} =70V, I _E =0
I _{CEX}	-	-	1.	mA	V _{CE} =70V, V _{EB(off)} =1.5V
I _{CEO}	-	-	700	uA	V _{CE} =30V, I _B =0
I _{EBO}	-	-	5	mA	V _{EB} =5V, I _C =0
*V _{CE(sat)1}	-	-	1.1	V	I _C =4A, I _B =400mA
*V _{CE(sat)2}	-	-	8.0	V	I _C =10A, I _B =3.3A
*V _{BE(on)}	-	-	1.8	V	I _C =4A, V _{CE} =4V
*h _{FE1}	20	-	100		I _C =4A, V _{CE} =4V
*h _{FE2}	5	-	-		I _C =10A, V _{CE} =4V
f _T	2	-	-	MHz	V _{CE} =10V, I _C =500mA, f=0.5MHz

*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%



Characteristics Curve





TO-220AB Dimension

3-Lead TO-220AB
Plastic Package
HSMC Package Code: E

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Date Code: M J E
 Control Code: 3 0 5 5 T

Note: Green label is used for pb-free packing
 Pin Style: 1.Base 2 & Tab.Collector 3.Emitter
 Material:
 • Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
 • Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

*: Typical, Unit: mm

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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _p)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{smin})	100°C	150°C
- Temperature Max (T _{smax})	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
T _{smax} to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60~150 sec	60~150 sec
Peak Temperature (T _p)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec